

## PRODUCTION OF THIN FILM TRANSISTOR MATRIX

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Inventor(s): KOSUGI KIYOHISA; others: 02  
Applicant(s): FUJITSU LTD  
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### Abstract

**PURPOSE:** To obtain a substrate for a TFT matrix system LCD which is low in cost and does not degrade TFT characteristics from mixing of impurities in liquid crystal.

**CONSTITUTION:** In a glass substrate for the TFT matrix system LCD, a soda lime glass substrate 1 covered with a transparent insulating protective film 2 at one side or both sides of the glass substrate surface is used, the transparent insulating protective film 2 is formed by ALD method, the transparent insulating protective films 2 are simultaneously formed on both sides of the soda lime glass substrate 1 by ALD method. Further, after forming a gate electrode 3 on the soda lime glass substrate 1 covered with the transparent insulating protective films 2, a transparent insulating film is formed as a gate insulating film 4 by ALD method and the transparent insulating film is also formed by ALD method for a final protective film 12.